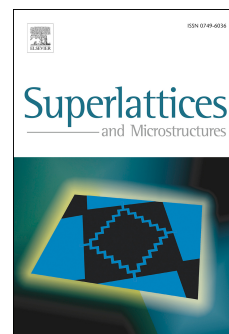


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Efficiency enhancement in AlGaIn deep ultraviolet light-emitting diodes by adjusting Mg doped staggered barriers

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Highlights

Mg-doped staggered barriers can improve the efficiency and rad recombination hugely.

The Mg-doped one has enhanced the performance better than the undoped one.

The best Al-content in the upper step of the p-type staggered barriers has been confirmed.

The root of low efficiency has been explored.

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